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WeEn Semiconductors





### 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT186A "full pack" plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Isolated package
- Low holding current for small load currents and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

### 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ t <sub>p</sub> = 20 ms; <u>Fig. 4; Fig. 5</u>	-	-	25	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 92$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	4	A
Static chara	cteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	2	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	2.5	5	mA





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### 4Q Triac

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{7}$	-	2.5	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	5	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.2	10	mA

## 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-71
2	T2	main terminal 2		Sym051
3	G	gate		
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BT136X-600D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A				

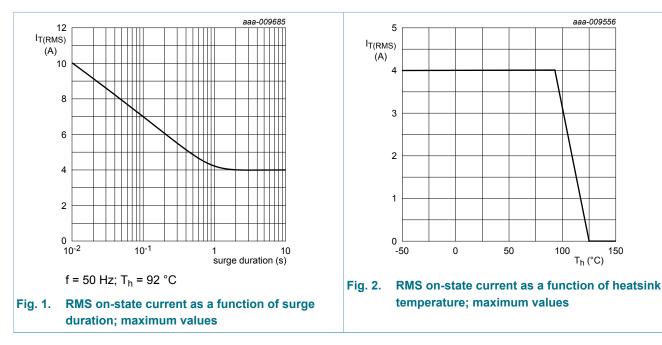
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### 7. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

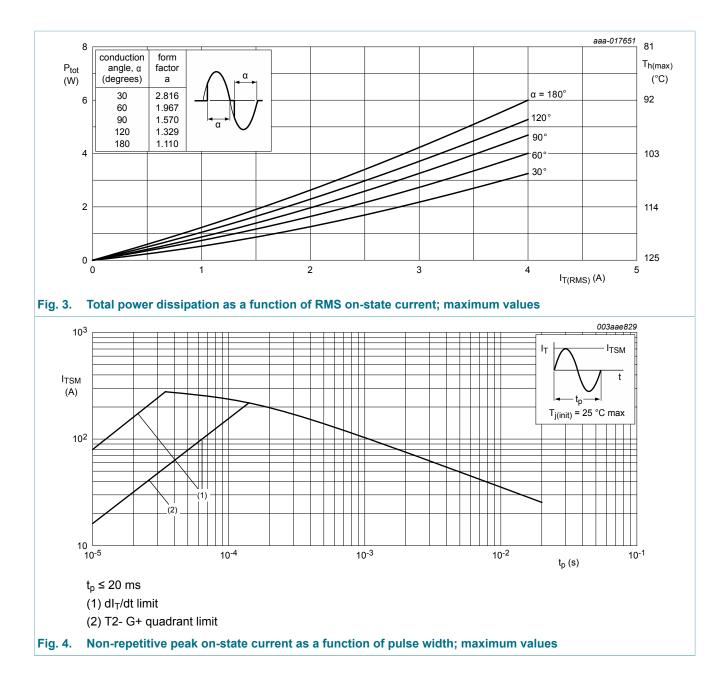
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 92$ °C; Fig. 1; Fig. 2; Fig. 3	-	4	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; Fig. 4; Fig. 5$	-	25	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	27	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	3.1	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 10 mA; T2+ G+	-	50	A/µs
		I <sub>G</sub> = 10 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G+	-	10	A/µs
		I <sub>G</sub> = 10 mA; T2- G-	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C





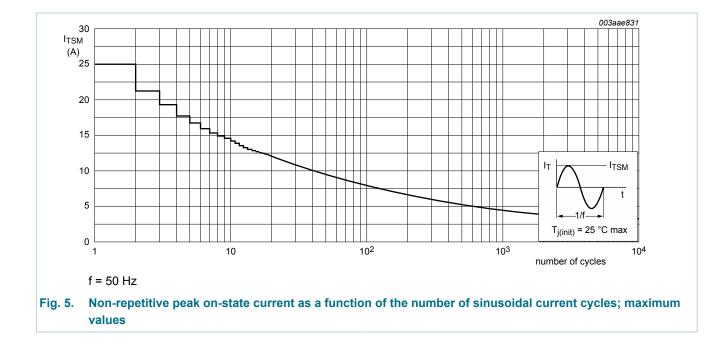
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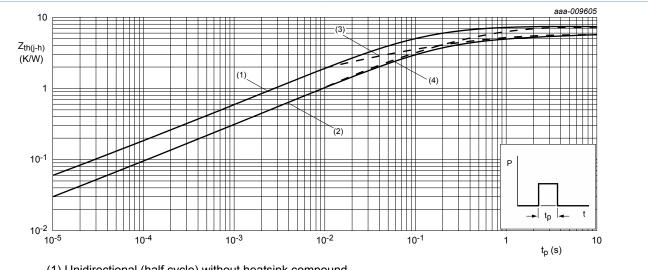
#### 4Q Triac



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### 8. Thermal characteristics

Table 5. T	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig. 6	-	-	5.5	K/W
	heatsink	full or half cycle; without heatsink compound; Fig. 6	-	-	7.2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



(1) Unidirectional (half cycle) without heatsink compound

(2) Bidirectional (full cycle) with heatsink compound

- (3) Unidirectional (half cycle) with heatsink compound
- (4) Bidirectional (full cycle) without heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

# 9. Isolation characteristics

Table 6. Isol	ation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

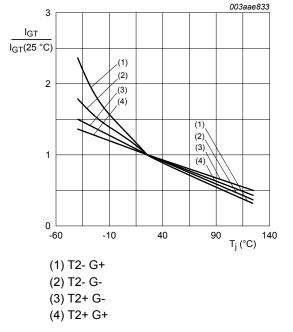
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### **10. Characteristics**

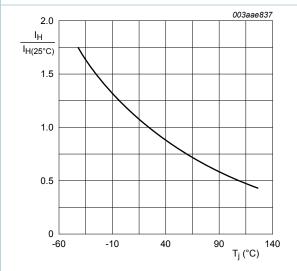
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; Fig. 7	-	2	5	mA
		$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; Fig. 7	-	2.5	5	mA
		$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; Fig. 7	-	2.5	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	5	10	mA
I <sub>L</sub> latchir	latching current	$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	1.6	10	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	1.2	15	mA
		$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; Fig. 8	-	2.2	10	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	1.2	15	mA
н	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.2	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
/ <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics	· · · · · · · · · · · · · · · · · · ·	I			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; T <sub>j</sub> = 125 °C; R <sub>GK</sub> = 1 kΩ; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	-	5	-	V/µs
gt	gate-controlled turn-on time	I <sub>TM</sub> = 6 A; V <sub>D</sub> = 600 V; I <sub>G</sub> = 0.1 A; dI <sub>G</sub> / dt = 5 A/us	-	2	-	μs

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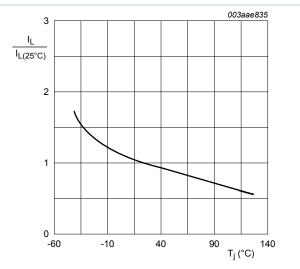
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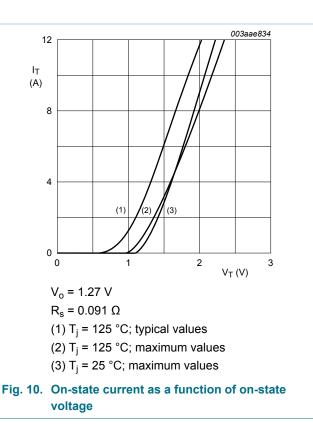






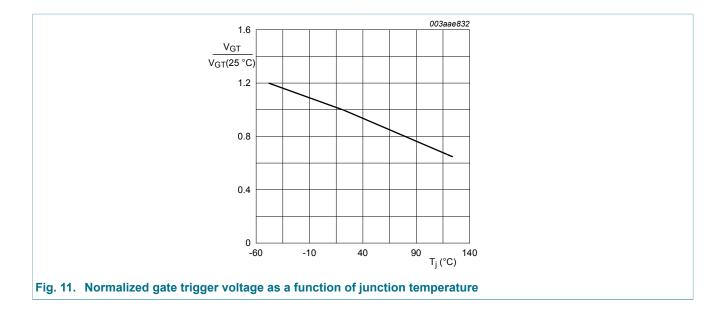






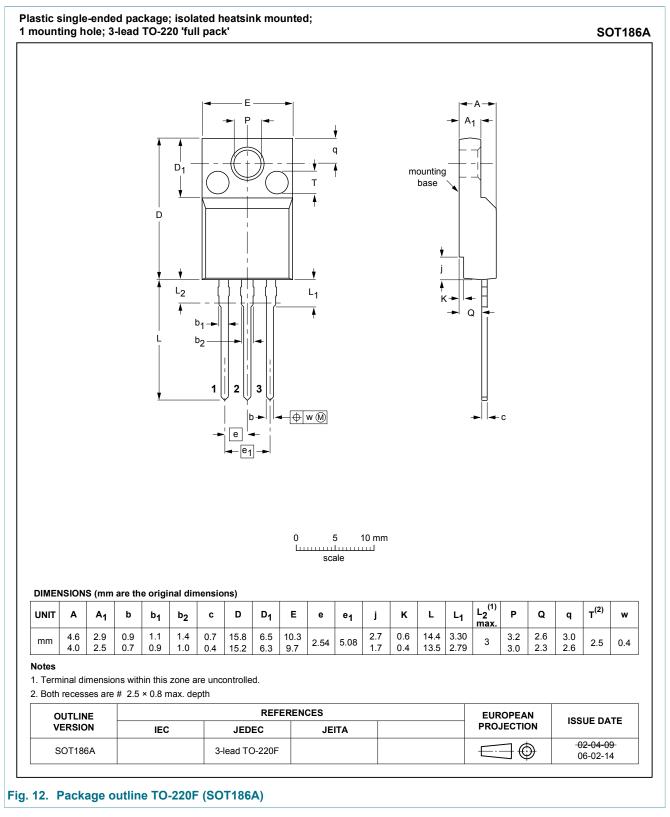
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### 4Q Triac





### **11. Package outline**



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#### **4Q Triac**

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